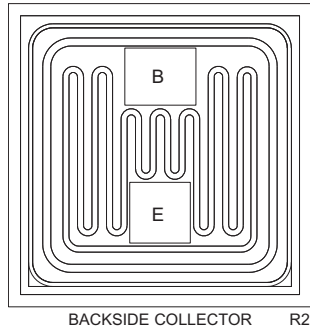


CP710V-2N6520

PNP - High Voltage Transistor Die

The CP710V-2N6520 is a silicon PNP transistor designed for high voltage applications.



MECHANICAL SPECIFICATIONS:

Die Size	26 x 26 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Size	6.1 x 4.9 MILS
Emitter Bonding Pad Size	5.2 x 5.2 MILS
Top Side Metalization	Al – 30,000Å
Back Side Metalization	Au – 9,000Å
Scribe Alley Width	2.2 MILS
Wafer Diameter	5 INCHES
Gross Die Per Wafer	25,214

MAXIMUM RATINGS: (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	350	V
Collector-Emitter Voltage	V _{CEO}	350	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Continuous Collector Current	I _C	500	mA
Continuous Base Current	I _B	250	mA
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS: (T_A=25°C)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CBO}	V _{CB} =250V		50	nA
I _{EBO}	V _{EB} =4.0V		50	nA
BV _{CBO}	I _C =100μA	350		V
BV _{CEO}	I _C =1.0mA	350		V
BV _{EBO}	I _E =10μA	5.0		V
V _{CE(SAT)}	I _C =10mA, I _B =1.0mA		0.30	V
V _{CE(SAT)}	I _C =20mA, I _B =2.0mA		0.35	V
V _{CE(SAT)}	I _C =30mA, I _B =3.0mA		0.50	V
V _{CE(SAT)}	I _C =50mA, I _B =5.0mA		1.0	V
V _{BE(SAT)}	I _C =10mA, I _B =1.0mA		0.75	V
V _{BE(SAT)}	I _C =20mA, I _B =2.0mA		0.85	V
V _{BE(SAT)}	I _C =30mA, I _B =3.0mA		0.90	V
V _{BE(ON)}	V _{CE} =10V, I _C =100mA		2.0	V
h _{FE}	V _{CE} =10V, I _C =1.0mA	20		
h _{FE}	V _{CE} =10V, I _C =10mA	30		
h _{FE}	V _{CE} =10V, I _C =30mA	30	200	
h _{FE}	V _{CE} =10V, I _C =50mA	20	200	
h _{FE}	V _{CE} =10V, I _C =100mA	15		

R0 (1-August 2016)

CP710V-2N6520

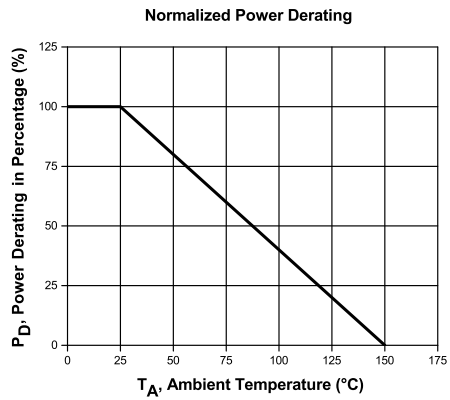
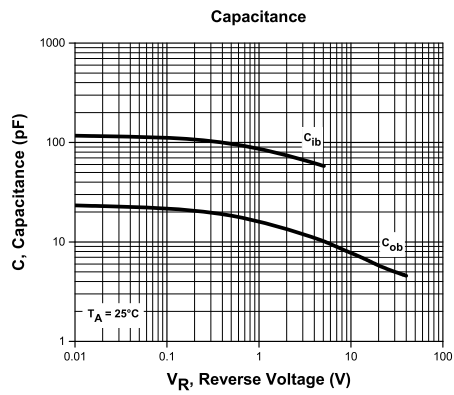
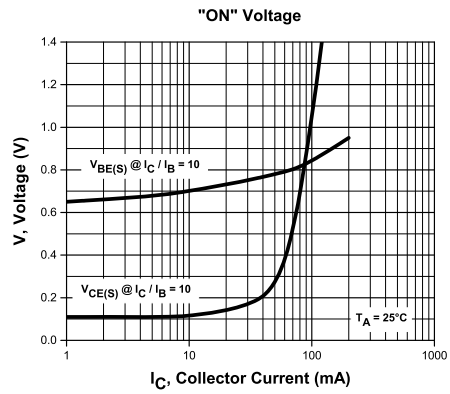
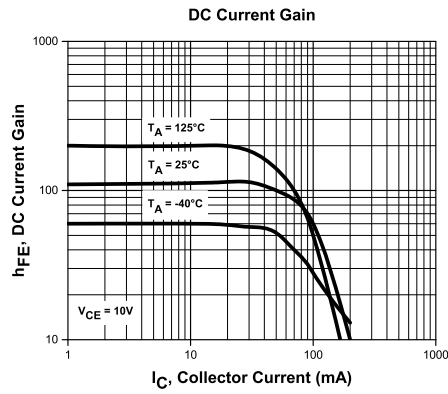
Typical Electrical Characteristics

ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$)

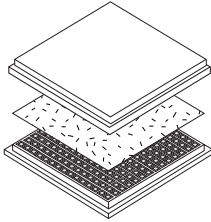
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
f_T	$V_{CE}=20\text{V}$, $I_C=10\text{mA}$, $f=20\text{MHz}$	40	200	MHz
C_{cb}	$V_{CB}=20\text{V}$, $I_E=0$, $f=1.0\text{MHz}$		6.0	pF
C_{eb}	$V_{EB}=0.5\text{V}$, $I_C=0$, $f=1.0\text{MHz}$		100	pF
t_{on}	$V_{CC}=100\text{V}$, $V_{BE}=2.0\text{V}$, $I_C=50\text{mA}$, $I_{B1}=10\text{mA}$		200	ns
t_{off}	$V_{CC}=100\text{V}$, $I_C=50\text{mA}$, $I_{B1}=I_{B2}=10\text{mA}$		3.5	μs

CP710V-2N6520

Typical Electrical Characteristics



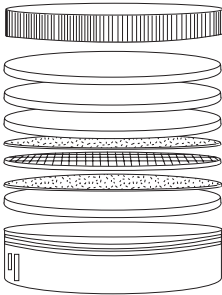
BARE DIE PACKING OPTIONS



BARE DIE IN TRAY (WAFFLE) PACK

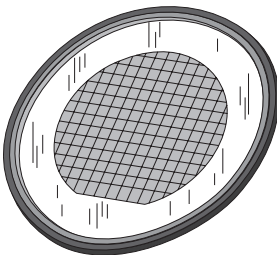
CT: Singulated die in tray (waffle) pack.
(example: CP211-PART NUMBER-CT)

CM: Singulated die in tray (waffle) pack 100% visually inspected as per MIL-STD-750, (method 2072 transistors, method 2073 diodes).
(example: CP211-PART NUMBER-CM)



UNSAWN WAFER

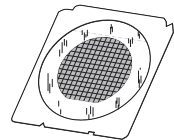
WN: Full wafer, unsawn, 100% tested with reject die inked.
(example: CP211-PART NUMBER-WN)



SAWN WAFER ON PLASTIC RING

WR: Full wafer, sawn and mounted on plastic ring,
100% tested with reject die inked.
(example: CP211-PART NUMBER-WR)

Please note: Sawn Wafer on Metal Frame (WS) is possible as a special order. Please contact your Central Sales Representative at 631-435-1110.



Visit the Central website for a complete listing of specifications:
www.centrasemi.com/bdspecs

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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